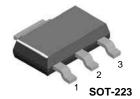


December 2009

FJT44 NPN Epitaxial Silicon Transistor

Features

· High Voltage Transistor



1. Base 2. Collector 3. Emitter

Absolute Maximum Ratings* T_A=25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CBO}	Collector-Base Voltage	500	V
V _{CEO}	Collector-Emitter Voltage	400	V
V _{EBO}	Emitter-Base Voltage	6	V
I _C	Collector Current	300	mA
P _C	Collector Dissipation (T _A = 25 °C)	2	W
TJ	Junction Temperature	150	°C
T _{STG} Storage Temperature Range		- 55 to +150	°C

^{*} These ratings are limiting values above which the serviceability of any semiconductor device may be impaired. **NOTES:**

Thermal Characteristics* T_A=25°C unless otherwise noted

Symbol	Parameter	Value	Units	
$R_{ hetaJA}$	Thermal Resistance, Junction to Ambient	62.5	°C/W	

^{*} Device mounted on FR-4 PCB 36 mm X 18 mm X 1.5 mm. mounting pad for the collector lead min. 6 cm²

Ordering Information

Part Number	Package	Packing size	Packing Method	Remarks
FJT44KTF	SOT-223	2500 pcs	Tape and Reel	
FJT44TF SOT-223		4000 pcs	Tape and Reel	

¹⁾ These ratings are based on a maximum junction temperature of 150°C.

²⁾ These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Electrical Characteristics* T_A = 25℃ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Units
BV _{CBO}	Collector-Base Breakdown Voltage	$I_C = 100 \mu A, I_E = 0$	500			V
BV _{CEO}	Collector-Emitter Breakdown Voltage	$I_C = 1 \text{mA}, I_B = 0$	400			V
BV _{EBO}	Emitter-Base Breakdown Voltage	$I_E = 100 \mu A, I_C = 0$	6			V
I _{CBO}	Collector-Base Cutoff Current	V _{CB} = 400V, I _E = 0			100	nA
I _{CES}	Collector-Emitter Cutoff Current	V _{CE} = 400V, V _{BE} = 0			500	nA
I _{EBO}	Emitter-Base Cutoff Current	$V_{CE} = 4V, I_C = 0$			100	nA
h _{FE}	DC Current Gain	$\begin{tabular}{lllllllllllllllllllllllllllllllllll$	40 50 45 40		200	
V _{CE(sat)}	Collector-Emitter Saturation Voltage	$I_C = 1 \text{mA}, I_B = 0.1 \text{mA}$ $I_C = 10 \text{mA}, I_B = 1 \text{mA}$ $I_C = 50 \text{mA}, I_B = 5 \text{mA}$			0.4 0.5 0.75	V V
V _{BE(sat)}	Base-Emitter Saturation Voltage	$I_C = 10$ mA, $I_B = 1$ mA			0.75	V
C _{obo}	Output Capacitance	$V_{CB} = 20V, I_{E} = 0, f = 1MHz$			7	pF

^{*} Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2.0%

Typical Performance Characteristics

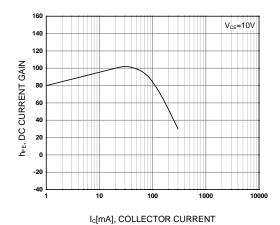


Figure 1. DC current Gain

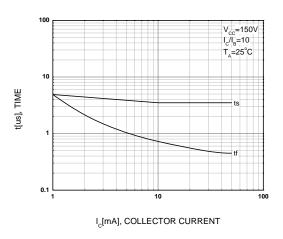


Figure 3. Turn-Off Switching Times

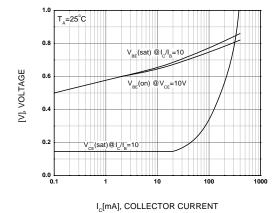


Figure 5. On Voltage

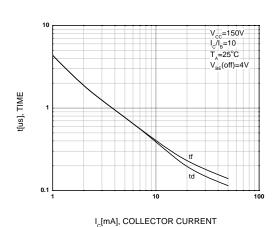


Figure 2. Turn-On Switching Times

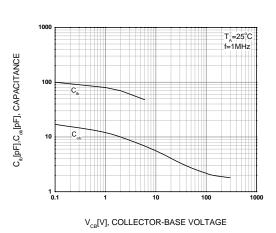


Figure 4. Capacitance

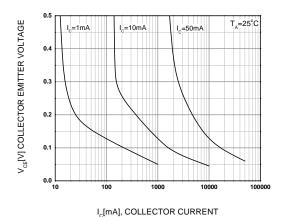


Figure 6. Collector Saturation Region

Typical Performance Characteristics (Continued)

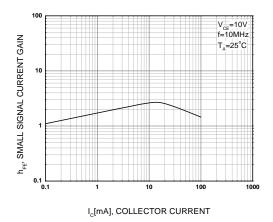
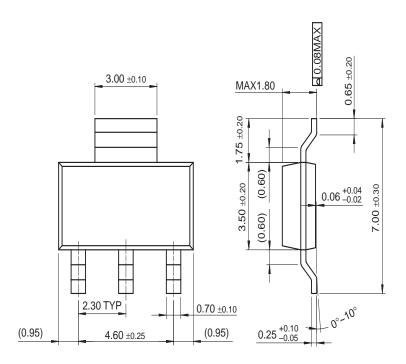
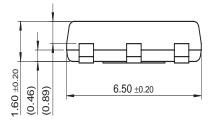


Figure 1. High Frequency Current Gain

Physical Dimensions

SOT-223





Dimensions in Millimeters





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